

Appl. No. 10/714,001  
Examiner: PHAM, THANHHA S, Art Unit 2813  
In response to the Office Action dated March 8, 2005

Date: July 5, 2005  
Attorney Docket No. 10113201

### AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph at page 4, line 18 with the following amended paragraph:

— In order to achieve the described objects, the present invention provides a method of forming a bit line contact via. First, a substrate having a transistor, comprising a gate electrode, drain region, and source region is provided. Then, a conductive layer is formed overlying the drain region, wherein the top surface of the conductive layer is lower than that of the gate electrode. Next, an insulating barrier layer is conformally formed overlying the substrate. Further, a dielectric layer is blanketly formed overlying the insulating barrier layer. Finally, a via is formed through the dielectric layer and insulating barrier layer, thereby exposing the conductive layer.